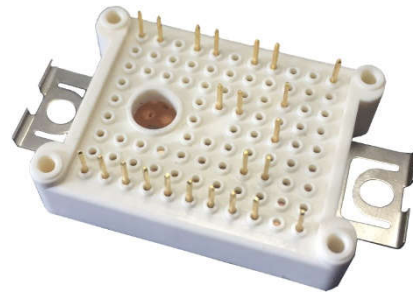


Preliminary Data

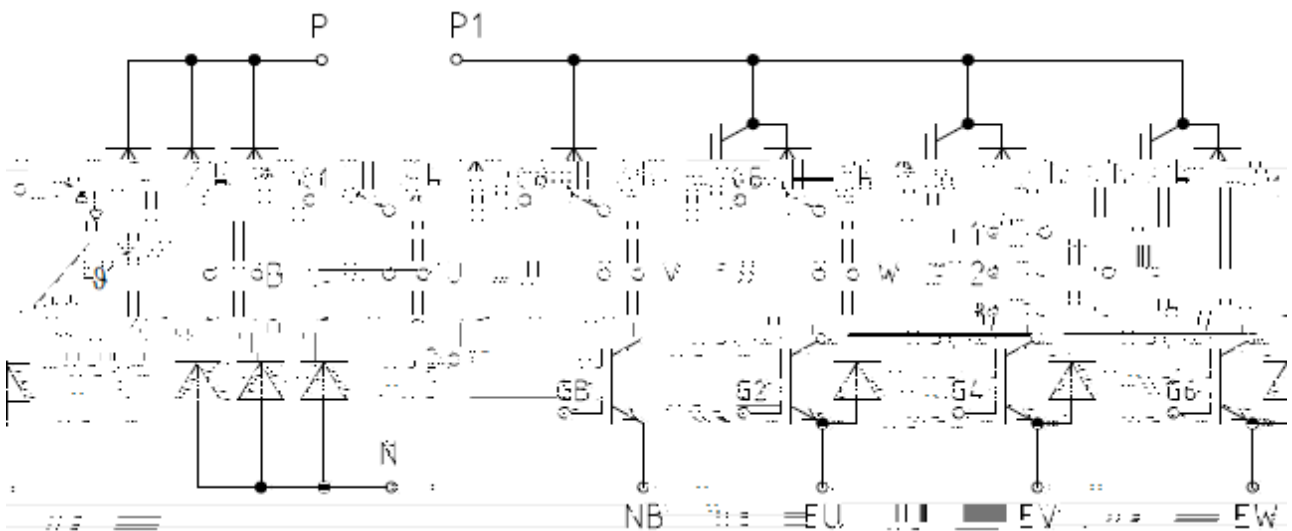
$V_{CES} = 1200V$

$I_C \text{ nom} = 15A / I_{CRM} = 30A$

- V_{CEsat} with positive temperature coefficient
- Low V_{CEsat}
- Low inductance case
- 10 μs short circuit capability
- Isolated copper baseplate using DBC technology



- Motor drivers
- Air Conditioning
- Auxiliary inverters



Parameter	Conditions	Symbol	Values	Units
Collector-emitter voltage	T _{vj} = 25°C	V _{CEs}	1200	V
Continuous DC collector current	T _C = 100°C, T _{vj} max = 175°C T _C = 25°C, T _{vj} max = 175°C	I _C	15 30	A
Repetitive peak collector current	t _p = 1 ms	I _{CRM}	30	A
Total power dissipation	T _C = 25°C, T _{vj} max = 175°C	P _{tot}	147	W
Gate-emitter peak voltage		V _{GE}	±20	V

Parameter	Conditions	Symbol	Values			Units
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	I _C = 15 A, V _{GE} = 15 V T _{vj} = 25°C T _{vj} = 150°C	V _{CEsat}		1.7 2.10		V
Gate threshold voltage	I _C = 0.48 mA, V _{CE} = V _{GE} T _{vj} = 25°C	V _{GEth}		5.9		V
Gate charge	V _{GE} = -15 / 15 V	Q _G		0.12		μC
Input capacitance	f = 1 MHz, T _{vj} = 25°C, V _{CE} = 25 V, V _{GE} = 0 V	C _{ies}		0.95		nF
Reverse transfer capacitance		C _{res}		0.04		nF
Collector-emitter cut-off current	V _{CE} = 1200 V, V _{GE} = 0 V, T _{vj} = 25°C	I _{CES}			1.0	mA
Gate-emitter leakage current	V _{CE} = 0 V, V _{GE} = 20 V, T _{vj} = 25°C	I _{GES}			400	nA
Turn-on delay time, inductive load	I _C = 15 A, V _{CE} = 600 V V _{GE} = -15 / 15 V , R _G = 20Ω T _{vj} = 25°C	t _{d on}		0.035		μs
Rise time, inductive load		t _r		0.03		μs
Turn-off delay time, inductive load		t _{d off}		0.09		μs
Fall time, inductive load		t _f		0.13		μs
Turn-on energy loss per pulse		E _{on}		1.75		mJ
Turn-off energy loss per pulse		E _{off}		0.4		mJ
SC data		V _{GE} ≤ 15 V, V _{CC} = 800 V t _p ≤ 10 μs, T _{vj} = 25°C	ISC		130	
Thermal resistance, junction to case	per IGBT	R _{thJC}		1.02	1.15	K/W
Thermal resistance, case to heatsink	per IGBT λ _{Paste} =1 W/(m·K) / λ _{grease} =1 W/(m·K)	R _{thCH}		1.02		K/W
Temperature under switching conditions		T _{vj op}	-40		150	°C

Parameter	Conditions	Symbol	Values	Units
Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	VRRM	1200	V
Continuous DC forward current		IF	15	A
Repetitive peak forward current	$t_p = 1 \text{ ms}$	IFRM	30	A

Parameter	Conditions	Symbol	Values			Units
			Min.	Typ.	Max.	
Forward voltage	$I_F = 15 \text{ A}, V_{GE} = 0 \text{ V}$ $T_{vj} = 25^{\circ}\text{C}$	V_F		2.00		V

Parameter	Conditions	Symbol	Values	Units
Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
Continuous DC collector current	$T_C = 100^{\circ}\text{C}, T_{vj} \text{ max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj} \text{ max} = 175^{\circ}\text{C}$	I_C	15 30	A
Repetitive peak collector current	$t_p = 1 \text{ ms}$	I_{CRM}	30	A
Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj} \text{ max} = 175^{\circ}\text{C}$	P_{tot}	147	W
Gate-emitter peak voltage		V_{CES}	± 20	V

Parameter	Conditions	Symbol	Values			Units
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$I_C = 15 \text{ A}, V_{GE} = 15 \text{ V}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_{CESat}		1.7 2.10		V
Gate threshold voltage	$I_C = 0.48 \text{ mA}, V_{CE} = V_{GE}$ $T_{vj} = 25^{\circ}\text{C}$	V_{GEth}		5.9		V
Gate charge	$V_{GE} = -15 / 15 \text{ V}$	Q_G		0.12		μC
Input capacitance	$f = 1 \text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}$	C_{ies}		0.95		nF
Reverse transfer capacitance		C_{res}		0.04		nF
Collector-emitter cut-off current	$V_{CE} = 1200 \text{ V}, V_{GE} = 0 \text{ V}, T_{vj} = 25^{\circ}\text{C}$	I_{CES}			1.0	mA
Gate-emitter leakage current	$V_{CE} = 0 \text{ V}, V_{GE} = 20 \text{ V}, T_{vj} = 25^{\circ}\text{C}$	I_{GES}				

T_{vj}

I I

I

Parameter	Conditions	Symbol	Values	Units
Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	VRRM	1200	V
Continuous DC forward current		IF	15	A
Repetitive peak forward current	$t_p = 1 \text{ ms}$	IFRM	30	A

Parameter	Conditions	Symbol	Values			Units
			Min.	Typ.	Max.	
Forward voltage	$I_F = 15 \text{ A}, V_{GE} = 0 \text{ V}$ $T_{vj} = 25^{\circ}\text{C}$	V_F		2.00		V
Peak reverse recovery current	$I_F = 15 \text{ A}, -d_{IF}/d_t = 1200 \text{ A}/\mu\text{s}$ $V_R = 600 \text{ V}, V_{GE} = -15 \text{ V}$ $T_{vj} = 25^{\circ}\text{C}$	I_{RR}		24		A
Recovered charge		Q_{RR}		1.8		μC
Reverse recovery energy		E_{rec}		0.35		mJ
Thermal resistance, junction to case	per diode	R_{thJC}		1.68	1.8	K/W
Thermal resistance, case to heatsink	per diode $I_{paste} = 1 \text{ W}/(\text{m}\cdot\text{K}) / I_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}		1.2		K/W
Temperature under switching conditions		$T_{vj op}$	-40		150	$^{\circ}\text{C}$

Parameter	Conditions	Symbol	Values			Units
			Min.	Typ.	Max.	
Rated resistance	$T_{NTC} = 25^{\circ}\text{C}$	R_{25}		5		k Ω
Deviation of R100	$T_{NTC} = 100^{\circ}\text{C}, R_{100} = 493 \Omega$	$\Delta R/R$	-5		5	%
Power dissipation	$T_{NTC} = 25^{\circ}\text{C}$	P_{25}			20	mW

Parameter	Conditions	Symbol	Values	Units
Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	VISOL	2.5	kV
Internal isolation	basic insulation (class 1, IEC 61140)		Al ₂ O ₃	
Creepage distance	terminal to heatsink terminal to terminal		11.5 6.3	mm
Clearance	terminal to heatsink terminal to terminal		10 5	mm
Comperative tracking index		CTI	>200	

Parameter	Conditions	Symbol	Values			Units
			Min.	Typ.	Max.	
Stray inductance module and fixture		L _{sCE}		28		nH
Module lead resistance, terminals - chip	TC = 25°C, per switch	R _{CC'+EE'} R _{AA'+CC'}		8 6		mΩ
Storage temperature		T _{stg}	-40		125	°C
Mountig force per clamp		F	20		50	N
Weight		G		24		g

